Characterization of charge collection in CdTe and CZT using the transient current technique

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A bstract

The charge collection properties in di erent particle sensor materials with respect to the shape of the generated signals, the electric eld within the detector, the charge carrier m obility and the carrier lifetim e are studied with the transient current technique (TCT). Using the well-known properties of Si as a reference, the focus is laid on Cadm ium -Telluride (CdTe) and Cadm ium -Zinc-Telluride (CZT), which are currently considered as promising candidates for the e cient detection of X-rays. A llm easurem ents are based on a transient-current technique (TCT) setup, which allows the recording of current pulses generated by an ²⁴¹Am source. These signals will be interpreted with respect to the build-up of space-charges inside the detector material and the subsequent deform ation of the electric eld. Additionally the in uence of di erent electrode materials (i.e. ohm ic or Schottky contacts) on the current pulse shapes will be treated in the case of CdTe. Finally, the e ects of polarization, i.e. the time-dependent degradation of the detector signals due to the accumulation of xed charges within the sensor, are presented.

1 Introduction

W hile Si is the standard sensor material for micro strip or pixel detectors for charged particle detection in high energy physics, its application to X -ray im aging is limited due to its low atomic number. Nevertheless, the concept of a directly converting sensor material in combination with a pixellated ASIC readout chip has caused a large interest in alternative sem iconductor materials like C dTe and CZT. In term s of stopping power these two materials prot their high atom ic numbers ($Z_{Cd} = 48$, $Z_{Zn} = 30$ and $Z_{Te} = 50$), but until recently their application for radiation detection has been limited due to the reduced material quality with respect to the collection of charges generated inside the material. With high quality C dTe and CZT now being commercially available,

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detailed studies of the charge carrier transport within the sensor material have been carried out in this paper.

Generally, signal generation by ionizing radiation in a sem iconductor detector is based on the creation of electron-hole pairs. The subsequent detection of the deposited charge is realized through the application of a potential di erence between the m etal contacts, which causes the generated charge carriers to driff. tow ards the oppositely charged electrode. In the case of a single channel, parallel plate detector thism eans, that the charge carrierm ovem ent causes a m easurable current signal immediately after the generation and separation of the electronhole pairs. P ractically all high energy particle experim ents integrate this current via a charge sensitive amplier, yielding an output voltage proportional to the created charge. This is where the transient-current technique di ers from the common approach. In a TCT setup a fast readout chain is used to directly amplify the current signal, as the charge carriers travel through the detector. The advantage of such a time-resolved current measurement over the common charge sensitive approach is the ability to directly m ap the charge carrier m ovem ent within the detector m aterial without any integration of the signal current. The discussion of the experimental results starts with a short introduction of the TCT-setup, followed by the presentation of the measured current pulses in section 3. Sections 5, 6 and 7 dealwith the analysis of the current signals.



2 The experim ental setup

Figure 1: Schematic view of the TCT-setup. The detector is replaced by its equivalent circuit diagram consisting of the detector resistance R_{Det} , the parasitic capacitance C_{Det}^{par} (' 1 pF) and a current source.

Figure 1 shows a schematic view of the experiment. A small, resistance-matched and shielded PCB provides the biasing network and the socket for the detector crystals. The signals coming from the sensor are AC-coupled to a commercial voltage am pli er (M iteq AM -1607-2000) with a gain of 41 dB.An ionizing particle creates a current signal within the detector. This current pulse is converted into a voltage pulse through the input im pedance (50) of the voltage am pli-

er, giving an overalltransim pedance gain of 5840 mV = A. The system s voltage noise is $(3.5 \quad 0.5) \text{ mV}_{\text{RM S}}$ at 2 G H z bandwidth. The am pli ed voltage pulses are stored in a broadband digital oscilloscope (Tektronix TDS 5104B 1 G H z). For further im provem ent of the noise characteristics, especially the quenching of electro-m agnetic pickup a second shielding box is placed around the PCB and the am pli er.

A llofthe follow ing m easurem entsuse 5.5 MeV -particles from an ^{241}Am -source in order to create electron-hole pairs within the detector. The main reason for this is the short penetration depth of -particles in matter (approx. 10-20 m

in C dTe), which guarantees a signal generation close to the irradiated electrode. This in turn enables the observation of purely electron or purely hole induced signals. In both cases one type of charge carriers traverses the whole detector volum e and thus generates the signal, whereas the oppositely charged type does not contribute to the signal as these carriers alm ost instantly reach the collecting electrode. A dditionally, the limited range of -particles allows the averaging overm any current pulses, because the starting conditions for each charge carrier m igration are the same for all events.

W ithin the short range of -particles also lies their major disadvantage, as the energy loss in the air and inside the source material itself cannot be neglected. Measurements with a conventional charge sensitive setup yield an average energy loss of 1.5 MeV 0.05 MeV for a detector-source distance of 10 mm air and a remaining -particle energy of 3.9 MeV 0.05 MeV (corresponding to 141 fC 1 fC in CdTe). By extrapolating the detector source distance to zero it is possible to determ ine the energy at which the -particles leave the ^{241}Am - source to about 4.7 MeV.

3 Current pulses

C urrent pulses in any kind of particle detector, whose operation is based on the induction of mirror charges on a certain number of electrodes, can be described by the Ram o-Shockley theorem [1, 2].

$$i(t) = Q_e(t) E_W q_{drift}^e(x(t)) + Q_{h+}(t) E_W q_{drift}^{p+}(x(t))$$
 (1)

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W ith ibeing the signal current, Q the electron or hole charge, $E_{\,W}\,$ the weighting

eld and $v_{\rm drift}$ the drift velocity. E_W only describes the coupling of the charge carrier m ovem ent to the readout electrode and is not to be confused with the electric eld E(x(t)), which determ ines the trajectory of the particles inside the detector. In the case of a single channel detector with parallel electrodes at a distance D, the expression for the weighting eld is reduced to the sim ple term 1/D. Solving the equation of motion for the created charge carriers under the

assumption of a linear electric eld distribution (caused by a constant spacecharge) yields an exponential current signal [3].

A part from a constant space-charge density inside the sensor material, charge carrier trapping can also in uence the pulse shape. Equation (1) states that the current amplitude i(t) is proportional to the deposited charge Q (t). Hence an exponential decay of the charge inside the detector again yields an exponential decay of the current amplitude [4].

3.1 Silicon

The properties of Sip-n diodes have previously been studied in detail [3, 5, 6]. In this work Sip-n diodes were used as reference devices for the studies on C dTe and C ZT. Figure 2 shows electron induced current pulses in a 1 mm thick Si diode, irradiated from the cathode (p+) side. The pulse durations range from 140 ns at 100 V down to 25 ns at 400 V, with maximum currents between 4 A and 8 A. For birth voltages the rising edge of the simuli is dominated



Figure 2: Electron signals in a 1 mm Sip-n diode. -particles impinging on the cathode.

by the signal electronics and the separation of the charge carriers (see section 62). This initial rising edge is followed by an exponential decay, caused by the negative space-charge inside the weakly doped n-type m aterial. The exponential decay ends upon the arrival of the set electrons at the anode, which can be seen as a more or less prom inent bend in the current signals (indicated by the arrow in Fig. 2). The subsequent naldrop of the am plitude is governed by the longitudinal di usion of the charge carriers, which has taken place during their



Figure 3: Hole signals in a 1 mm Sip-n diode.-particles impinging on the anode.

m ovem ent through the detector. For low voltages the charge carrier cloud can reach larger dimensions and, as a consequence, the signal falls o slow ly after the

rst carriers arrive at the electrode. The spike at t = 0 is a trigger artifact. The full depletion voltage of these diodes was determ ined by capacity measurements ($C_{\rm FD} = 12 \, {\rm pF} - 1 \, {\rm pF}$) and by ts to the pulse shape and lies at 96 V 5 V. For voltages su ciently above the full depletion bias ($V_{\rm bias} > 300 \, {\rm V}$) hole signals are observed. Figure 3 shows signals that were recorded with the anode (n-side) being irradiated by the -particles. The signic cantidely at the beginning of the signal is caused by the low electric eld in the anode region.

3.2 Cadm ium -Telluride

A total of four C dTe detector crystals with two di erent electrode con gurations were analyzed with the presented T C T -setup. The rst pair, named C dTeO, has P latinum (Pt) electrodes on both sides, providing an ohm ic contact behavior. The second set of crystals, here labelled as C dTe-S, has an Indium (In) electrode on the backside and a regular Pt contact on the topside. A llavailable C dTe and C ZT samples are glued to a ceram ic holder, thus allowing only the irradiation of the top Pt electrode. A ccordingly, hole signals cannot be observed with the C dTe-S sensors, as these detectors need a reverse bias for operation. F igures 4 and 5 show electron signals in C dTe-O and C dTe-S for di erent bias voltages. It is evident that while the maxim um am plitudes for identical bias settings are of com parable height, the pulse shapes clearly depend on the type of contact electrodes. Furtherm ore, it is im portant to mention that the maxim um am plitude for C dTe-S does not coincide with the arrival of the charge carriers at the electrode. The implications of this elect will be further discussed in sections 6 and 7. The observation of hole-induced current pulses in CdTe is di cult due to the very low hole mobility ($_{\rm h}$ ' 100 cm²/Vs). Nevertheless, Fig. 5 shows hole signals that were recorded with a CdTe-O sensor at voltages close to the maximum bias of about 300 V and with currents below 1 A.



Figure 4: Electron signals in CdTe-O with cathode irradiation (D = 500 m).



Figure 5: Hole signals in CdTe-O with anode irradiation (D = 500 m).



Figure 6: Electron signals in CdTe-S with cathode irradiation. The dashed line shows a signal from an ohm ic CdTe crystal (D = 500 m).

3.3 Cadm ium -Zinc-Telluride



Figure 7: Electron signals in CZT with cathode irradiation (D = 2 mm).

Figure 7 shows electron signals in a 2 mm thick CZT sample manufactured by eV-P roducts. The displayed curves resemble the electron signals in Si and CdTe-O, indicating a similar space-charge distribution in all three detector types. The current amplitude is lower than in CdTe because of the lower electric eld, which also explains the lack of hole signals for CZT. The range of the applicable voltages extends up to 900 V, as above this bias the leakage current slow ly increases.

4 Collected charge

The total collected charge is determined by a numerical integration over the recorded current pulses, which can be converted into the deposited energy. The overall precision of this energy measurement is given by three factors:

$$tot = 2 + 2 + 2 + 2 = 108 \text{ keV}$$
 (2)

In the current setup the precision of the charge m easurem ent is dom inated by the error in the detector-source distance, caused by the alignm ent of the 241 Am - source and the sensor crystal. A future in provem ent of the alignm ent precision w ill reduce the uncertainty in the deposited energy, but currently the error due to the detector-source m isalignm ent is $_{\rm dist}$ ' 100 keV. A nother factor that in-

uences the experim ental precision is the statistical uctuation of the -particles energy loss in air $_{\rm air}$, which is approximately 30 keV in the setup. The last contribution to the overall error is $_{\rm int}$. $_{\rm int}$ param eterizes the error in the integration over the current pulses due to variations in the length of the integration intervaland is estimated to be 27 keV. In total this results in a precision of the charge collection m easurem ents of approximately 3%. The m easured collected



Figure 8: Collected charge as a function of applied bias for di erent m aterials. Expected am ount of collected charge, i.e. 100 % collection e ciency, given by dashed lines.

charge or energy can how ever be sm aller than the original -particle energy, as charge trapping m ay occur.

As can be seen from Fig. 8, the measured collected charges in all investigated materials saturate at higher bias. These saturation values have to be compared with the expected amount of charge that is deposited by a 3.9 MeV -particle (141 fC in CdTe and 136 fC in CZT). For the investigated Sip-n diodes the average electron-hole pair creation energy has been measured in [7] to be 3.8 eV 0.6 eV, giving a deposited charge of about 164 fC. A lthough this value is slightly above the established 3.62 eV, the saturation value of 164 fC in Fig. 8 supports this result. For C dTe and C ZT the deposited charges agree well with the expected amount of charge, leading to the conclusion that both sem iconductor materials do not show measurable electron trapping. Based on this

nding, the shape of the current pulses has to be interpreted in terms of space charges (see section 6). From the lack of trapping also follows, that the average lifetime $_{\rm cc}$ and the average mean free path $_{\rm cc}$ exceed the pulse duration and the detector width, respectively.

5 M obilities

A part from the m easurem ent of the collected charge, the recorded current pulses also allow the determ ination of the charge carrier mobility via the pulse duration t_E . At this point the m athem atical treatment for Si and C dTe slightly di ers, as the electric eld dependence of has to be taken into account. It has been shown, that deviates from its constant behavior above 2 kV/cm in Si [6] and above approx. 12 kV/cm in C dTe [8]. The condition for a non-constant m obility was only met for Si, so that two di erent form ulae were used:

$$C_{dT e=C Z T} = \frac{D^2}{t_r V}$$
(3)

$$s_{i} = \frac{D^{2}}{2t_{E}V_{FD}} \ln \frac{V + V_{FD}}{V V_{FD}} - 1 - \frac{x_{0}}{D}\frac{2V_{FD}}{V + V_{FD}}$$
(4)

The error in the determ ination of the charge carrier mobility comes from the determ ination of the transit time t_E . From Fig. 9 it is evident that the charge carrier mobilities in Si show the expected eld dependence and that the electron mobilities in CdTe and CZT remain constant up to 6 kV/cm. A verages over the measured mobilities yield electron mobilities of (956 29) cm²/Vs for CdTeO-1 and (1022 24) cm²/Vs for CdTeO-2, a hole mobility of (72 11) cm²/Vs in CdTeO-1 and an electron mobility of (990 25) cm²/Vs in CZT. The values for Si lie within 5% of the values calculated by an empirical form ula [6] (at T = 27 C). For CZT the measured electron mobilities agree well with the 1000 cm²/Vs stated by the manufacturer. Sim ilar details on the electron and hole mobilities in the CdTe samples were not available from the manufacturer, so that them easured values have to be compared with the results of other groups. These literature values [8, 9] lie around $_e = (1000 - 1100) \text{ cm}^2/\text{V} \text{ s and} _h ' 100 \text{ cm}^2/\text{V} \text{ s, well in agreement with the results reported here.}$



Figure 9: Charge carrier mobilities in di erent sem iconductors

6 E lectric F ield

The electric eld pro le in a single channel sensor crystal can be deduced from a current pulse under the prem ise of a point-like charge cloud and the absence of charge carrier trapping. W ith this prerequisite it is possible to calculate the charge carrier position x (t) from the num erical integral over a current pulse:

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$$Q(t_{E}) = \int_{0}^{Z_{t_{E}}} i(t)dt = \frac{Q_{0}}{D} \int_{0}^{Z_{t_{E}}} \frac{dx(t)}{dt}dt = \frac{Q_{0}}{D} (x(t_{E}) - x(0))$$
(5)

 Q_0 is the integrated charge up to the time t_E , where the bend in the current signal occurs and Q_0 is the total collected charge. From (5) follows the electric eld pro le along the charge carriers path:

$$E(x(t)) = \frac{i(x(t)) D}{Q_0}$$
(6)

6.1 Si

Fig. 10 shows the measured (solid lines) and the theoretical (dashed lines) electric eld pro les in the n-doped part of the Sip+ n diodes at three different bias settings. The theoretical eld distributions [3] were calculated with a depletion voltage $V_{FD} = 96 V$ and a starting position of the charge carriers $x(0) = 20 \text{ m} \cdot As$ expected, the measured eld strengths decrease linearly from the cathode towards the anode, based on the constant positive space-charge density in the fully depleted n-type material. Fits to the constant slopes of the eld pro les give a space-charge density of (3.3 0.65) x 10^{10} cm 3 . The the-



Figure 10: M easured (solid curves) and theoretical (dashed lines) electric eld distributions in the n-type region of a 1 mm thick Sip+ n diode for three di erent voltages. E lectrons start at the left and progress toward the anode (right).

ory of the p-n junction does not support the presence of a negative space-charge inside the n-doped m aterial. Therefore the deviations of the m easured electric eld from the theoretical expectation close to the cathode have to be explained

by two other e ects.

i) Lim ited bandwidth of the TCT -setup. The bandwidth of the system has been tested by injecting voltage pulses with rise times of 500 ps into the circuit. The system s overallbandwidth is measured to be about 500 M Hz. Therefore current pulse rise times of more than 3 ns cannot be explained by the electronics alone.

ii) Plasma e ect. One -particle creates approx. 12 million electron-hole pairs along a cylindrical track of about 10-20 m length. These charge carriers are not separated instantly as they shield the external electric eld, which then causes the charge carrier migration to start with a delay on the order of several hundred picoseconds to several nanoseconds. D i erent authors [10, 11, 12, 13] measured the in uence of the plasma e ect on the charge collection for -particles with energies below 10 M eV.

Therefore the distortion of the measured electric eld close to the cathode has to be a feature of the experim ental method and not of the material itself. This experim ental limitation of the transient current technique is hard to overcome, as TCT measurements need large signal charges. This means that only -particles and lasers are valid signal sources, but the use of a laser is problem atic because

of the surface treatm ent and the m etal electrodes of the crystals. N evertheless, the very good agreem ent between prediction and m easurem ent shows, that the determ ination of the electric eld from a TCT-m easurem ent is valid.

6.2 CdTe-O

Figure 11 shows the measured electric eld pro les in CdTe-O at three di erent voltages. All curves display a maximum close to the middle of the detector, followed by a linear decrease in eld strength towards the anode. From Fig. 11 can be seen, that the electric eld pro le to the right of the maximum follows a linear behavior. U sing Poisson's equation the space-charge density in this region can be calculated. The results are given in Table 1.



However, the electric eld deviates from this linear behavior close to the

Figure 11: Measured and tted electric eld pro les inside a 500 m thick C dTe-O sensor. A node on the right.

cathode. This eld pro le can be explained by two e ects. First, the presence of two oppositely charged space charges inside the detector. That is, a negative space-charge in front of the cathode and a positive one next to the anode. The origin of these opposing charges could be the injection of charge carriers through both ohm ic contacts [14]. Second, the plasm a e ect, which is the main reason for the deviation of the electric eld pro le close to the cathode in Si. In order to determ ine which e ect dom inates the electric eld behavior it was tried to reconstruct the measured current pulses under the assumption that only the plasm a e ect is responsible for the deviations close to the cathode and that the true electric eld inside the crystals is a linear extrapolation of the ts in Fig. 11. The reconstructed current pulses were calculated based on the R am o-

Shockley theorem and a simple, rst-order model of the plasm a e ect, based on two time-constants:

i) Reduced signal charge and charge carrier velocity. As the dense charge cloud erodes the shielding e ect is weakened. Thus, the num ber of charge carriers Q (t) that contribute to the current signal rises exponentially with time. A dditionally the reduced electric eld inside the charge cloud causes a reduction in the charge carrier velocity. Therefore, the charge carriers do not move with the velocity dom inated by the externally applied bias, but rather pick up speed as the density of the charge cloud degrades. These two e ects are parameterized by exponential functions with the time-constant . A much more detailed model can be found in [10].

ii) D elayed signal form ation. The movem ent of the charge carriers does not start immediately after their generation, but is delayed by several nanoseconds [12, 13]. This shift is given by t_s .

$$i(t) = Q(t) - E(x(t)) = Q_0(1 e^{t}) - (a x(t) + b)$$
 (7)

$$E(x(t)) = a x(t) + b$$
 (8)

$$x(t) = \frac{b}{a} + (x_0 - \frac{b}{a}) e^{a} (t t_s) (1 - e^{t})$$
 (9)



Figure 12:M easured and reconstructed current pulses in a 500 $\,$ m thick CdTe-O sensor at 300 V bias.

Fig. 12 shows the results of the reconstruction at 300 V bias. The solid line represents the measured curve, whereas the dotted line indicates the expected

current signal without the above model for the plasm a e ect. The dashed line shows the fully reconstructed signals with plasm a e ect. The observed timeconstants are comparable to the values reported by [12, 13]. In addition, the measurements support an inverse electric eld dependence of the plasm a e ect, which was also found by [12, 13]. A though a nalanswer regarding the electric

ed pro le close to the cathode can not be given, the results of the current pulse reconstruction indicate, that the plasm a e ect can not be discarded as a reason for the observed eld behavior.

As a conclusion, the agreement between the electric eld proles presented herein and the results from other electric eld measurements [15, 16] proves, that the electric eld strength in C dTe-O has a maximum in the vicinity of the cathode.

CdTe-O	V _{bias} [V]	100	150	200	250	300	
	$N_{\rm D}$ [10 ¹¹ cm ³]	2.37	4.07	5.35	7.35	8.69	
	$N_{\rm D}$ [10 ⁹ cm ³]	1.88	2.35	2.39	1.34	2.37	
	t _s [ns]	4.0	2.3	1.6	1.0	0.85	
	[ns]	4.0	22	1.6	0.9	8.0	
CZT	V _{bias} [V]	300	400	500	600	700	800
	$N_{\rm D}$ [10 ¹¹ cm ³]	0.61	0.97	1.22	1,28	1.46	1.58
	$N_{\rm D}$ [10 ⁸ cm ³]	3.04	4.86	6.56	3.83	3.61	4.09

Table 1: Space-charge densities in CdTe-O and CZT. The model parameters t_s and were obtained from ts with t_s ' 0.2 ns and t_s ' 0.1 ns.

6.3 CdTe-S

As stated above, the calculation of the electric $\,$ eld relies on the determ ination of the arrival time t_E . For CdTe-S this is more complicated than for CdTe-O and CZT, because the CdTe-S crystals do not show an easily identiable arrival of the electrons at the anode. A librough the curves show a pronounced maximum, it is unlikely that this bend in the current signals indicates the arrival time t_E .

The basis for this assumption is that the two crystal types di er only in their contact electrodes. From (1) then follows, that a di erence in the current am – plitude can only be caused by a di erence in the electric eld pro le. The direct comparison of the current pulses in Fig. 6 shows, that the maximum and average am plitudes in CdTe-O and CdTe-S are equal, which also means, that the average transit times have to be comparable. Therefore the average signal durations (transit time $t_{\rm E}$) in CdTe-S were taken to be in the order of the respective signal durations in CdTe-O. Based on this noting Fig. 13 shows the electric

eld pro les in C dTe-S for di erent bias settings. In contrast to the eld pro le in C dTe-O the electric eld in C dTe-S has a m in im um at the cathode from where it rises, before it falls o again close to the anode. The rising portion of the



Figure 13: M easured (solid lines) and tted (dashed lines) electric eld pro les inside a 500 m thick C dTe-S sensor. A node on the right.

electric eld agrees with the expectation, as the Schottky-contact of these sensors is good enough to be blocking for holes [17, 18]. Consequently the ohm ic cathode injects electrons into the crystal, generating a negative space-charge and a rising electric eld. The measured break-down of the electric eld close to the anode does not agree with this expectation, but can again be interpreted in terms of a positive space-charge. The reason for this positive space-charge might be the enhanced emission of holes through the anode into the crystal at high electric elds. In that case the conduction properties of the sensor would be space-charge and recombination controlled [19].

6.4 CZT

Figure 14 shows the electric eld distribution inside a 2 mm thick CZT crystal. The situation is similar to CdTe-O with the maximum eld strength close to the cathode and a linearly decreasing electric eld towards the anode.

7 Polarization

During the measurements it became evident, that the CdTe-S sensors su er from a signi cant decrease in signal amplitude, if they are operated at a low voltages for a longer time. This can be attributed to the polarization of the detector, i.e. the gradual accumulation of xed space-charges inside the detector. These space-charges deform the electrical eld up to a point where the operation of the detector becomes impossible. None of the other tested materials showed this behavior, which is why this section will only deal with the CdTe-S sensors.



Figure 14: M easured (solid lines) and extrapolated (dashed lines) electric eld pro les inside a 1 mm thick CZT sensor. A node on the right.

Figure 15 shows the e ect of the polarization on the current pulses. W ith ongoing operation of the detector the initial knee (1 st arrow) in the pulse shape is lost and the current am plitude is reduced. In addition to this, the position of the maximum current am plitude w ith respect to the beginning of the signal is barely changed. This means, that although the overall electric eld strength in the sensor is reduced, the maximum eld strength is still reached after the same time. Considering the reduced charge carrier velocity under a reduced

eld strength, it follows that the position of the maximum electric eld strength in the sensor is shifted towards the cathode. If the position of the maximum was xed, i.e. would lie at the anode, it should take more than twice as long for it to be reached after 30 m ins of operation as compared to 0 m ins. This is clearly not supported by the observed current pulses.

The second feature of the current signals is that they develop a bend in the falling slope (2 nd arrow). This and the change in the position of the maximum electric eld strength both speak in favor of the argument, that the charge carriers reach

the electrode only after the maximum current amplitude has occurred. The electrode only after the maximum current amplitude has occurred. The electrode only after the maximum current amplitude has occurred. At 50 V bias the charge-sensitive setup stopped recording the pulses after only 4 m ins of operation. Switching of the bias for a few seconds neutralizes the polarization and causes the process to begin again.



Figure 15: E ect of polarization on current signals at 200 V in a 500 m thick CdTe-S sensor. Over 30 m inutes the signal amplitude decreases signi cantly, whereas the signal duration increases.



Figure 16: M easured collected charge over time for three dimensions. The m easurem ents were performed with a charge sensitive setup and a 500 m thick CdTe-S sensor.

U sing the same form alism as in section 6 it is possible to observe the timewise behavior of the electric eld inside a CdTe-S sensor (see Fig. 17). The gure shows that the externally applied electric eld is gradually compensated and that the position of the maximum eld strength is shifted from the middle of the sensor crystal towards the cathode. A possible explanation for the shift of the maximum s position could again be the injection of holes through the anode and the time-dependent expansion of this space-charge towards the cathode. These results are in contrast to the models [20, 21], which assume the build-up of a negative space-charge in front of the anode and the resulting reduction of the electric eld. The models further imply that the major part of the detector volume shows a low eld strength and that only the region in front of the anode possesses a high electric eld.



Figure 17: Changes in the electric eld of a 500 m thick CdTe-S sensor due to polarization at + 200 V. A node on the right.

8 Conclusions

In sum m ary, this paper presented a TCT-study of Si, CdTe and CZT. It was found, that the investigated crystals do not show m easurable electron trapping, indicating a m aterial quality that is suitable for particle detection. Furtherm ore it was shown that the electric eld pro les in ohm ic CdTe, in Schottky-contacted CdTe-S and in CZT can be approxim ated by linear relations and that all detectors feature space-charges inside the bulk m aterial. Finally, it was dem onstrated that Schottky-contacted CdTe sensors show a signi cant polarization at low voltages, which m akes the operation at high bias necessary.

9 A cknow ledgem ents

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